



### STFI15N65M5 Information



For Reference Only

Part Number STFI15N65M5
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N CH 650V 11A I2PAKFP **Package** TO-262-3 Full Pack, I2Pak

Package TO-262-3 Full Pack, I2Pak
For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## STFI15N65M5 Specifications

| Manufacturer Part Number         STFI15N65M5           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-262-3 Full Pack, 12Pak           Series         MDmesh? V           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         22nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         816pF @ 100V           Vgs (Max)         ±25 V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         340 mOhm @ 5.5A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         12PAKFP (TO-281)           Package / Case         TO-262-3 Full Pack, 12Pak  |  |                                      |
|---|--|--------------------------------------|
| Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-262-3 Full Pack, 12Pak  Series  MDmesh? V  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Forin to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  11A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  10V  Vgs (Max)  10V  Vgs (Max)  10V  Vgs (Max)  10V  10V  10V  10V  10V  10V  10V  10  | Manufacturer Part Number               | STF115N65M5                          |
| Package         TO-262-3 Full Pack, 12Pak           Series         MDmesh? V           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         22nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         816pF @ 100V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         340 mOhm @ 5.5A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         12PAKFP (TO-281)           Package / Case         TO-262-3 Full Pack, 12Pak  | Manufacturer                           | STMicroelectronics                   |
| Package         TO-262-3 Full Pack, 12Pak           Series         MDmesh? V           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         22nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         816pF @ 100V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         340 mOhm @ 5.5A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         12PAKFP (TO-281)           Package / Case         TO-262-3 Full Pack, 12Pak  | Category                               | Discrete Semiconductor Products      |
| Series MDmesh? V FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 816pF @ 100V Vgs (Max) ±25V FET Feature Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 340 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAKFP (TO-281) Package / Case   |  | Transistors - FETs, MOSFETs - Single |
| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds816pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs340 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKFP (TO-281)Package / CaseTO-262-3 Full Pack, 12Pak  | Package                                | TO-262-3 Full Pack, I2Pak            |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds816pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs340 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKFP (TO-281)Package / CaseTO-262-3 Full Pack, 12Pak   | Series                                 | MDmesh? V                            |
| Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds816pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs340 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKFP (TO-281)Package / CaseTO-262-3 Full Pack, I2Pak  | FET Type                               | N-Channel                            |
| Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 250μA  Gate Charge (Qg) (Max) @ Vgs  1nput Capacitance (Ciss) (Max) @ Vds  Ngs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30W (Tc)  Rds On (Max) @ Id, Vgs  340 mOhm @ 5.5A, 10V  Operating Temperature  Nounting Type  Through Hole  Supplier Device Package  Package / Case  11A (Tc)  10V  10V  10V  21PACP  10V  10V  10V  10PACP  10PACP | Technology                             | MOSFET (Metal Oxide)                 |
| Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds816pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs340 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKFP (TO-281)Package / CaseTO-262-3 Full Pack, I2Pak   | Drain to Source Voltage (Vdss)         | 650V                                 |
| Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  816pF @ 100V  Vgs (Max)  ±25V  FET Feature  - Power Dissipation (Max)  30W (Tc)  Rds On (Max) @ Id, Vgs  340 mOhm @ 5.5A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  I2PAKFP (TO-281)  Package / Case  TO-262-3 Full Pack, I2Pak   | Current - Continuous Drain (Id) @ 25°C | 11A (Tc)                             |
| Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  816pF @ 100V  Vgs (Max)  ±25V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  340 mOhm @ 5.5A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  I2PAKFP (TO-281)  Package / Case  TO-262-3 Full Pack, I2Pak   | Drive Voltage (Max Rds On, Min Rds On) | 10V                                  |
| Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  I2PAKFP (TO-281)  Package / Case  TO-262-3 Full Pack, I2Pak  | Vgs(th) (Max) @ Id                     | 5V @ 250μA                           |
| Vgs (Max) ±25V  FET Feature -  Power Dissipation (Max) 30W (Tc)  Rds On (Max) @ Id, Vgs 340 mOhm @ 5.5A, 10V  Operating Temperature 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package I2PAKFP (TO-281)  Package / Case TO-262-3 Full Pack, I2Pak  | Gate Charge (Qg) (Max) @ Vgs           | 22nC @ 10V                           |
| FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 340 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAKFP (TO-281) Package / Case TO-262-3 Full Pack, I2Pak  | Input Capacitance (Ciss) (Max) @ Vds   | 816pF @ 100V                         |
| Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  I2PAKFP (TO-281)  Package / Case  TO-262-3 Full Pack, I2Pak   | Vgs (Max)                              | ±25V                                 |
| Rds On (Max) @ Id, Vgs340 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKFP (TO-281)Package / CaseTO-262-3 Full Pack, I2Pak  | FET Feature                            | -                                    |
| Operating Temperature 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package I2PAKFP (TO-281)  Package / Case TO-262-3 Full Pack, I2Pak  | Power Dissipation (Max)                | 30W (Tc)                             |
| Mounting Type Through Hole Supplier Device Package I2PAKFP (TO-281) Package / Case TO-262-3 Full Pack, I2Pak  | Rds On (Max) @ Id, Vgs                 | 340 mOhm @ 5.5A, 10V                 |
| Supplier Device Package I2PAKFP (TO-281) Package / Case TO-262-3 Full Pack, I2Pak   | Operating Temperature                  | 150°C (TJ)                           |
| Package / Case TO-262-3 Full Pack, I2Pak  | Mounting Type                          | Through Hole                         |
|   | Supplier Device Package                | I2PAKFP (TO-281)                     |
| Report errors?  | Package / Case                         | TO-262-3 Full Pack, I2Pak            |
|   |  | Report errors?                       |

#### STFI15N65M5 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# STFI15N65M5 Payment Methods



















### STFI15N65M5 Shipping Methods













If you have any question about STFI15N65M5, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com